

Ultrafast high voltage rectifier

Features

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching and conduction losses
- Insulated package:
 - Electrical insulation = 2500 V rms
 - Capacitance = 189 pF

Description

The STTH20004TV1 uses ST new 400 V technology and is specially suited for use in switching power supplies, welding equipment, and industrial applications, as an output rectification diode.

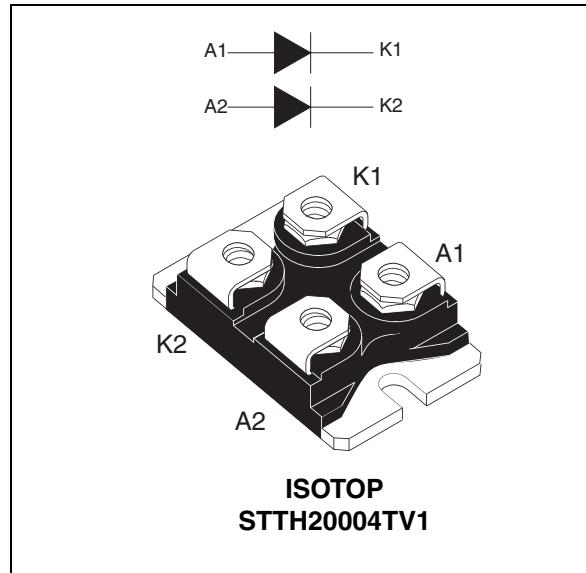


Table 1. Device summary

Symbol	Value
$I_{F(AV)}$	Up to 2 x 120 A
V_{RRM}	400 V
$T_j(\max)$	150 °C
V_F (typ)	0.83 V
t_{rr} (typ)	60 ns

1 Characteristics

Table 2. Absolute ratings (limiting values, per diode)

Symbol	Parameter			Value	Unit
V _{RRM}	Repetitive peak reverse voltage			400	V
I _{F(RMS)}	Forward rms current			200	A
I _{F(AV)}	Average forward current, $\delta = 0.5$	T _c = 90 °C	Per diode	100	A
		T _c = 73 °C	Per diode	120	
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms Sinusoidal		900	A
T _{stg}	Storage temperature range			-55 to + 150	°C
T _j	Maximum operating junction temperature			150	°C

Table 3. Thermal parameter

Symbol	Parameter		Maximum	Unit
R _{th(j-c)}	Junction to case	Per diode	0.50	°C/W
		Total	0.30	
R _{th(c)}	Coupling		0.10	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j \text{ (diode1)} = P_{\text{(diode1)}} \times R_{\text{th(j-c)}} \text{ (per diode)} + P_{\text{(diode2)}} \times R_{\text{th(c)}}$$

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
I _R ⁽¹⁾	Reverse leakage current	T _j = 25 °C	V _R = V _{RRM}			100	μA
		T _j = 125 °C			100	1000	
V _F ⁽²⁾	Forward voltage drop	T _j = 25 °C	I _F = 100 A			1.2	V
		T _j = 150 °C			0.83	1.0	

1. Pulse test: t_p = 5 ms, δ < 2 %

2. Pulse test: t_p = 380 μs, δ < 2 %

To evaluate the maximum conduction losses use the following equation:

$$P = 0.8 \times I_{F(AV)} + 0.002 I_{F(RMS)}^2$$

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit	
t_{rr}	Reverse recovery time	$T_j = 25^\circ\text{C}$	$I_F = 1 \text{ A},$ $dI_F/dt = 50 \text{ A}/\mu\text{s},$ $V_R = 30 \text{ V}$		75	100	ns
			$I_F = 1 \text{ A},$ $dI_F/dt = 200 \text{ A}/\mu\text{s},$ $V_R = 30 \text{ V}$		45	60	
t_{fr}	Forward recovery time	$T_j = 25^\circ\text{C}$	$I_F = 100 \text{ A},$ $dI_F/dt = 200 \text{ A}/\mu\text{s}$		800	ns	
V_{FP}	Forward recovery voltage		$V_{FR} = 1.1 \times V_{F\max}$		2.6	V	
I_{RM}	Reverse recovery current	$T_j = 125^\circ\text{C}$	$I_F = 100 \text{ A},$ $dI_F/dt = 100 \text{ A}/\mu\text{s},$ $V_R = 200 \text{ V}$		18	A	
S_{factor}				0.4		-	

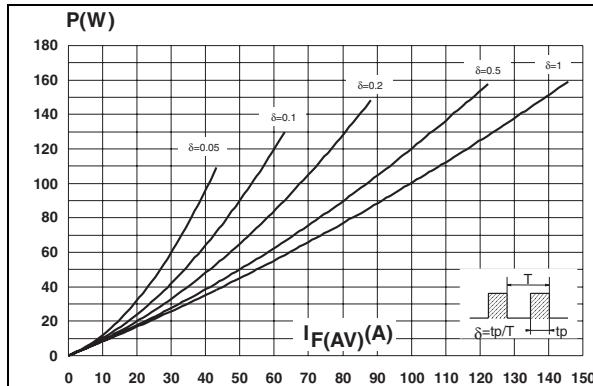
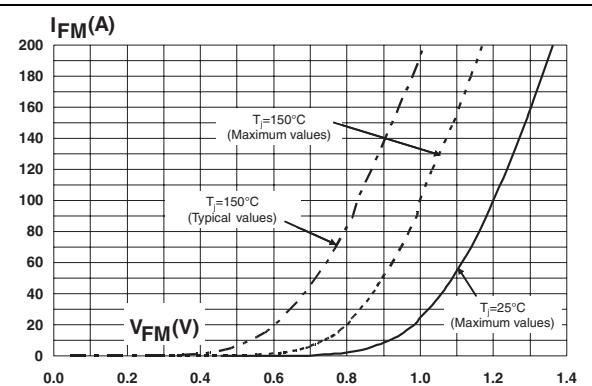
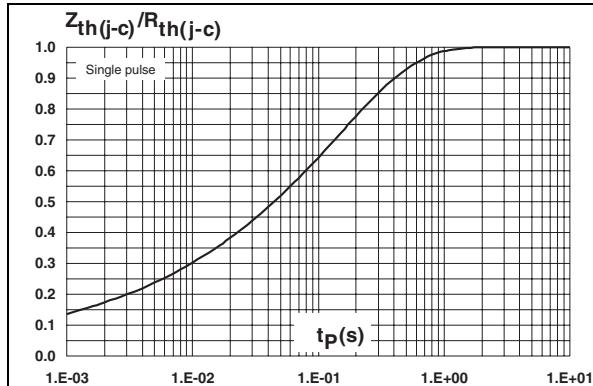
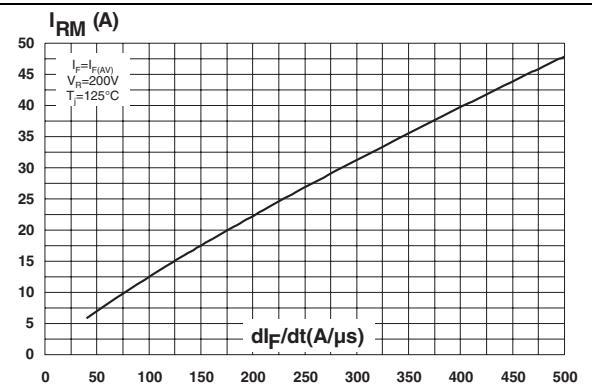
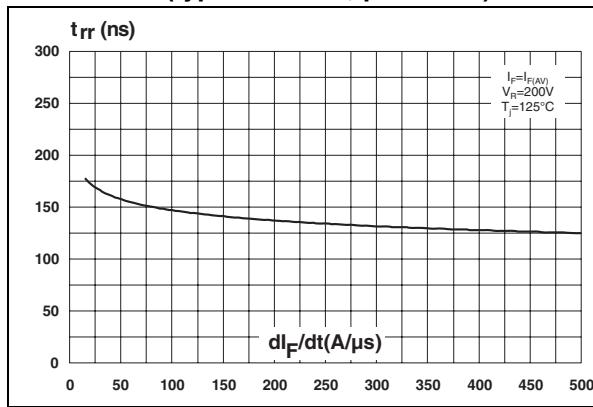
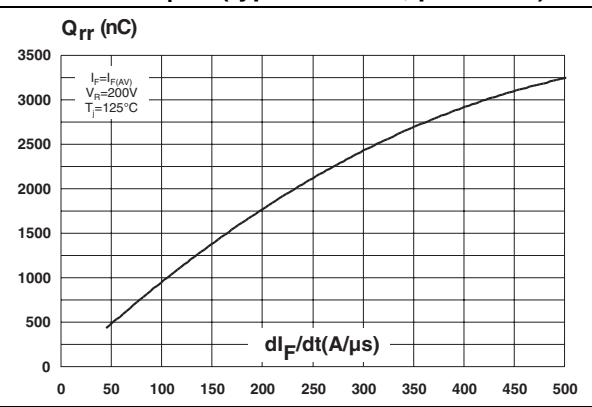
Figure 1. Conduction losses versus average forward current (per diode)**Figure 2. Forward voltage drop versus forward current (per diode)****Figure 3. Relative variation of thermal impedance junction to case versus pulse duration****Figure 4. Peak reverse recovery current versus dI_F/dt (typical values, per diode)****Figure 5. Reverse recovery time versus dI_F/dt (typical values, per diode)****Figure 6. Reverse recovery charges versus dI_F/dt (typical values, per diode)**

Figure 7. Reverse recovery time versus dI_F/dt (typical values, per diode)

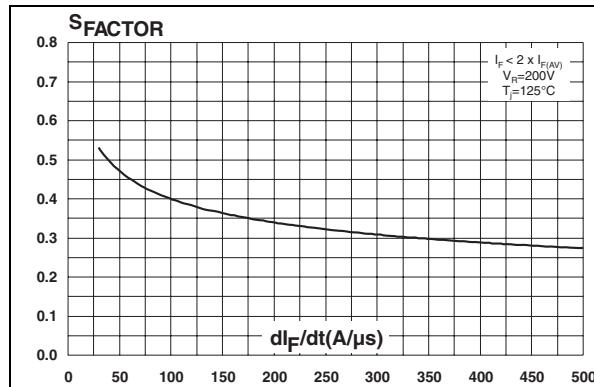


Figure 9. Transient peak forward voltage versus dI_F/dt (typical values, per diode)

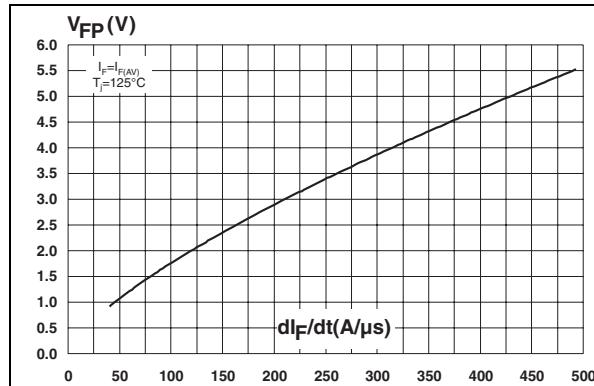


Figure 8. Relative variations of dynamic parameters versus junction temperature

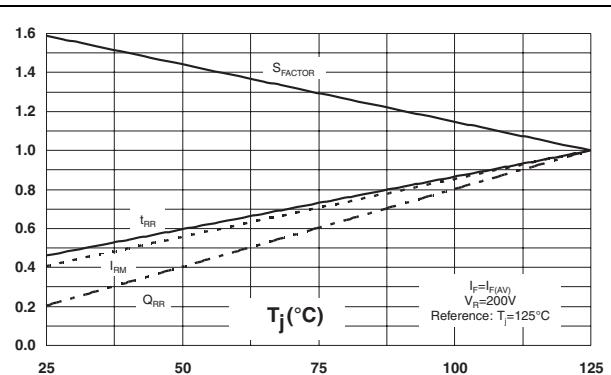


Figure 10. Forward recovery time versus dI_F/dt (typical values, per diode)

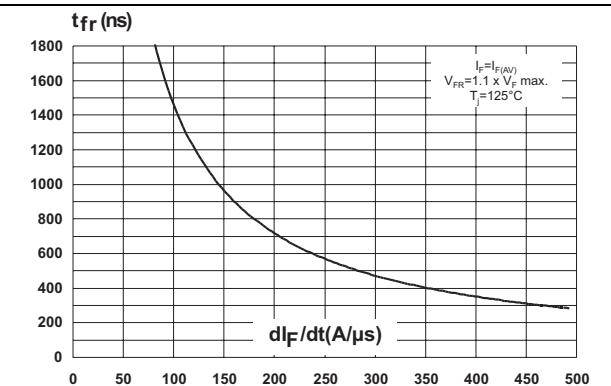
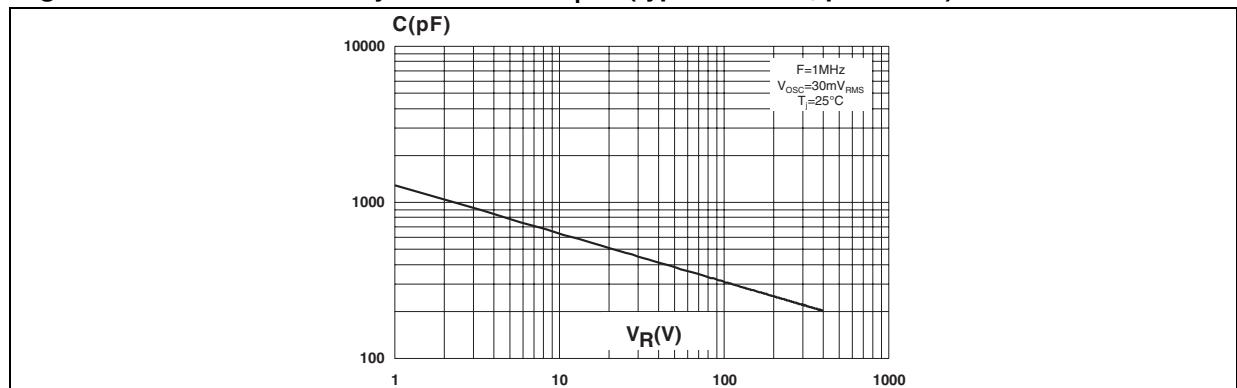


Figure 11. Reverse recovery time versus dI_F/dt (typical values, per diode)

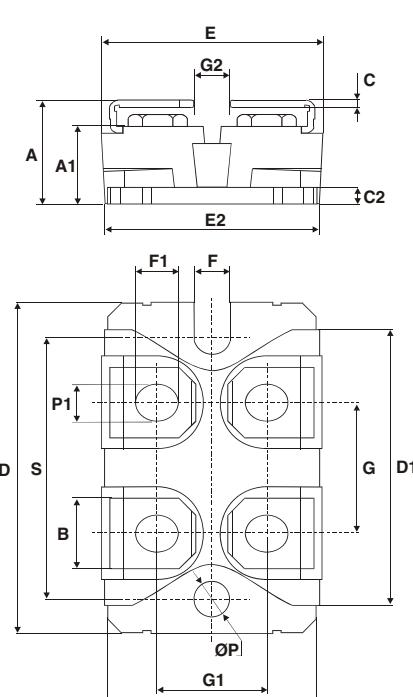


2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK® is an ST trademark.

Table 6. ISOTOP dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193



3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH20004TV1	STTH20004TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
18-Oct-2005	1	First issue.
15-Sep-2011	2	Added insulated package information in <i>Features</i> .

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